

ITC1100 1000 WATT, 50V, Pulsed Avionics 1030 MHz

GENERAL DESCRIPTION CASE OUTLINE 55SW, Style 1 The ITC1100 is a common base bipolar transistor. It is designed for pulsed **Common Base** interrogator systems in the frequency band of 1030 MHz. The device has gold thin-film metallization for proven high MTTF. The transistor includes input returns for improved output rise time . Low thermal resistance package reduces junction temperature which extends the life time of the product. **ABSOLUTE MAXIMUM RATINGS Power Dissipation** Device Dissipation¹ @25°C (P_d) 3400 W Thermal Resistance¹ (θ_{IC}) .08°C/W Voltage and Current Collector-Base Voltage 65V Emitter-Base Voltage 3.5V Collector Current¹ 80A **Temperatures** -40 to +150°C Storage Temperature Operating Junction Temperature¹ +200°C

ELECTRICAL CHARACTERISTICS @ 25°C

| SYMBOL | CHARACTERISTICS | TEST CONDITIONS | MIN | ТҮР | MAX | UNITS |
|--------------------|--------------------------------------|--------------------|-----|-----|-----|-------|
| BVebo ² | Emitter-Base Breakdown(open) | Ie=50mA | 3.5 | | | V |
| BVces | Collector-Emitter Breakdown(shorted) | Ic=30mA | 65 | | | V |
| BVceo ² | Collector-Emitter Breakdown (open) | Ic=30mA | 30 | | | V |
| ${h_{\rm FE}}^2$ | DC Current Gain | Ic=5A, Vce=5V | 20 | | 100 | β |

FUNCTIONAL CHARACTERISTICS @ 25°C

| G _{PB} | Common Base Power Gain | $V_{cc} = 50V, F = 1030MHz,$ | 10 | 10.5 | | dB |
|------------------|---|------------------------------------|--------------|------|-----|----|
| | | Pout=1000W Peak Min, PW=1µS, DF=1% | | | | |
| η_{c} | Collector Efficiency | $V_{cc} = 50V, F = 1030MHz,$ | 45 | 50 | | % |
| | | Pout=1000W Peak Min, PW=1µS, DF=1% | | | | |
| t _r | Rise Time | $V_{cc} = 50V, F = 1030MHz,$ | | 50 | 80 | nS |
| - | | Pout=1000W Peak Min, PW=1µS, DF=1% | | | | |
| VSWR | Output Load Mismatch | $V_{cc} = 50V, F = 1030MHz,$ | | | 4:1 | Ψ |
| | | Pout=1000W Peak Min, PW=1µS, DF=1% | | | | |
| Z_{in} | Series Input Impedance (Circuit | $V_{cc} = 50V, F = 1030MHz,$ | 0.89 – j2.3 | | Ω | |
| | source impedance @ test cond.) | Pout=1000W Peak Min, PW=1µS, DF=1% | 5 | | | |
| Z _{out} | Series Output Impedance (Circuit load impedance @ test cond.) | $V_{cc} = 50V, F = 1030MHz,$ | 0.54 - j2.64 | | Ω | |
| | | Pout=1000W Peak Min, PW=1µS, DF=1% | 3 | | | |

¹ At rated output power and pulse conditions

² Not measurable due to EB Returns

